
Oral presentation | 21 Joint Session K "Wide bandgap oxide semiconductor materials and devices" | 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

[10a-Z20-1~12]21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

Yutaka Furubayashi(Kochi Univ. of Tech.), Hiroyuki Nishinaka(Kyoto Inst. of Tech.)

Thu. Sep 10, 2020 9:00 AM - 12:15 PM Z20

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

12:00 PM - 12:15 PM

[10a-Z20-12][The 42nd JSAP Young Scientist Award Speech] Hot carrier effects in InGaZnO thin-film transistor

○Takanori Takahashi¹, Ryoko Miyanaga¹, Mami N. Fujii¹, Jun Tanaka², Kazushige Takechi², Hiroshi Tanabe², Juan Paolo Bermundo¹, Yasuaki Ishikawa^{1,3}, Yukiharu Uraoka¹ (1.NAIST, 2.Tianma Japan, Ltd., 3.Aoyama Gakuin Univ.)

Keywords:oxide semiconductor, thin-film transistor, reliability